

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MSC81250M** is Designed for DME/TACAN Applications up to 1150 MHz.

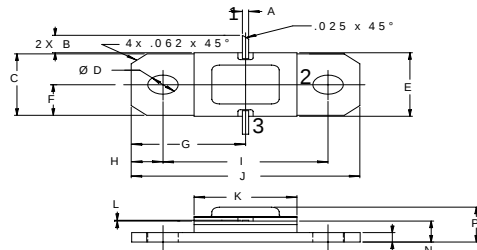
FEATURES:

- Internal Input/Output Matching Networks
- $P_G = 6.2$ dB at 250 W/1150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	17.8 A
V_{CC}	55 V
P_{DISS}	600 W @ $T_C \leq 80^\circ C$
T_J	$-65^\circ C$ to $+250^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$
θ_{JC}	0.2 $^\circ C/W$

PACKAGE STYLE .400 2NL FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.020 / 0.51	.030 / 0.76
B	.100 / 2.54	
C	.376 / 9.55	.396 / 10.06
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F		.193 / 4.90
G		.450 / 11.43
H		.125 / 3.18
I	.640 / 16.26	.660 / 16.76
J	.890 / 22.61	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.004 / 0.10	.007 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

1 = Collector 2 = Base 3 = Emitter

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10$ mA	65			V
BV_{CER}	$I_C = 25$ mA $R_{BE} = 10 \Omega$	65			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CES}	$V_{CE} = 50$ V			25	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	15		120	---
P_G	$V_{CC} = 50$ V $P_{IN} = 250$ W $f = 1025 - 1150$ MHz	6.2	6.5		dB
η_c		40	38		%
P_{OUT}		250	270		W